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Notice of Allowability	Application No.	Applicant(s)	
	10/552,102	HANNA ET AL.	
	Examiner	Art Unit	
	Elias Ullah	2812	
The MAILING DATE of this communication app. All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this a or other appropriate communication IGHTS. This application is subject	pplication. If not included on will be mailed in due cours	e. THIS he initiative
1. This communication is responsive to <u>10/17/2007</u> .		, ; ,	
2. The allowed claim(s) is/are <u>1-19</u> .	•		
3.			
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Attachment(s) 1. Notice of References Cited (PTO-892)	5. Notice of Informal	Patent Application	
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. 🔲 Interview Summar	y (PTO-413),	
3. ⊠ Information Disclosure Statements (PTO/SB/08), Paper No./Mail Date 10/3/2005	Paper No./Mail D 7. ⊠ Examiner's Amend	ate dment/Comment	
4. Examiner's Comment Regarding Requirement for Deposit of Biological Material Output Description: Description: Output Description: Des	8. ⊠ Examiner's Staten 9. □ Other	nent of Reasons for Allowand	:e
		Page Sec. 3	

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DETAILED ACTION

This office action is in response to an election restriction requirement filed on 10/17/2007.

Election/Restrictions

Applicant's election without traverse of claims 1-19 in the reply filed on 10/17/2007 is acknowledged.

This application is in condition for allowance except for the presence of claims 20-28 directed to an invention non-elected without traverse. Accordingly, claims 20-28 has been cancelled.

EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

Cancel claims 20-28.

Allowable Subject Matter

Claims 1-19 are allowed.

REASONS FOR ALLOWANCE

The following is an examiner's statement of reasons for allowance: with respect to claim 1, there is no prior art available or obvious motivation to combine elements of prior art which teach disposing a GaAs single crystal as a substrate in a metal

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organic chemical vapor deposition (MOCVD) reactor; preparing Al, Ga, In vapors by thermally decomposing organomctallic compounds of Al,Ga, and In; preparing Zn vapors by thermally decomposing an organomctallic Zn compound; preparing P vapors by thermally decomposing phosphine gas; simultaneously supplying the Al, Ga, In, P, Se, and Zn vapors to a region for epitaxial crystal growth on the substrate; and epitaxially growing a GaAlInP crystal doped with Zn and Se on the substrate; wherein flow rates of the Zn and Se vapors supplied to the region for epitaxial crystal growth are controlled to produce a heavily doped GaAlInP compound semiconductor with Zn serving as a p-type dopant at an atomic ratio of Zn:Se greater than two in the GaAlInP crystal. Claims 2-9 are dependent on claim 1.

The following is an examiner's statement of reasons for allowance: with respect to claim 10, there is no prior art available or obvious motivation to combine elements of prior art which teach disposing a GaAs single crystal as a substrate in a metal organic chemical vapor deposition (MOCVD) reactor; preparing AI, Ga, In vapors by thermally decomposing organometallic compounds of AIGa, and In; preparing P vapors by thermally decomposing phosphine gas; preparing group II element vapors by thermally decomposing an organometallic group IIA or IIB compound; preparing group VIB vapors by thermally decomposing a gaseous compound of group VIB; simultaneously supplying the AI, Ga, In, P, Se, and Zn vapors to a region for epitaxial crystal growth on the substrate; wherein the group IIA or IIB and group VIB vapors supplied to the region for epitaxial crystal growth produce a cdoped GaAIInP compound semiconductor with a group IIA or IIB element serving

as a p-type dopant having low group II atomic diffusion at an atomic ratio of II:VI greater than approximately two in the GaAlInP crystal. Claims 11-19 are dependent on claim 10.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Elias Ullah whose telephone number is (571) 272-1415. The examiner can normally be reached on weekdays, between 8AM-5PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, MICHAEL LEBENTRITT can be reached on (571) 272-1873. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

E. Ullah, 11/5/2007

SCOTT B. GEYER PRIMARY EXAMINER

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